MTR5R8N06SD

10-JUN-2019

SGT N-channel Power MOSFET

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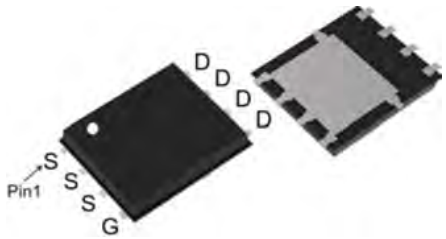
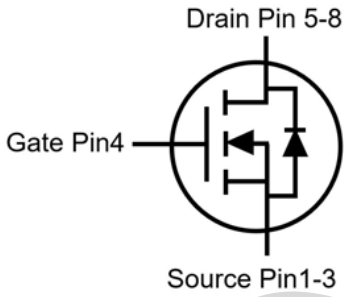
PDFN5x6





V_{DS}	60	V
$R_{DS(on),TYP}$@ V_{GS}=10 V	4.6	mΩ
I_D	90	A

Features

1、Low on – resistance
2、High power package (PDFN5X6)
3、SGT N-channel Power MOSFET
4、Halogen free

Applications

1、Load Switch for Portable Devices
2、DC/DC Converter

Maximum ratings, at T_A =25°C, unless otherwise specified

Symbol	Parameter		Rating	Unit
$V_{(BR)DSS}$	Drain-Source breakdown voltage		60	V
V_{GS}	Gate-Source voltage		±20	V
I_{AS}	Avalanche Current	T_C =25°C	32	A
I_D	Continuous drain current @VGS=10V	T_C =25°C	90	A
		T_C =100°C	57	A
I_{DM}	Pulse drain current tested ①	T_C =25°C	269	A
EAS	Avalanche energy, single pulsed ②		51	mJ
P_D	Maximum power dissipation	T_C =25°C	83	W
T_{STG},T_J	Storage and Junction Temperature Range		-55 to 150	°C

Thermal Characteristics

Symbol	Parameter	Rating	Unit
$R_{\theta JC}$	Thermal Resistance, Junction-to-Case	1.2	°C/W
$R_{\theta JA}$	Thermal Resistance, Junction-to-Ambient	45	°C/W

Electrical Characteristics

Symbol	Parameter	Condition	Min.	Typ.	Max.	Unit
Static Electrical Characteristics @Tj=25°C (unless otherwise stated)						
$V_{(BR)DSS}$	Drain-Source Breakdown Voltage	V_{GS}=0V, I_D=250μA	60	--	--	V
I_{DSS}	Zero Gate Voltage Drain Current	V_{DS}=48V,V_{GS}=0V	--	--	1	μA
I_{GSS}	Gate-Body Leakage Current	V_{GS}=±20V,V_{DS}=0V	--	--	±100	nA
$V_{GS(th)}$	Gate Threshold Voltage	V_{DS}=V_{GS},I_D=250μA	1.2	1.7	2.5	V
$R_{DS(on)}$	Drain-Source On-State Resistance ④	V_{GS}=10V, I_D=20A	--	4.6	5.8	mΩ
		V_{GS}=4.5V, I_D=15A	--	6.0	7.5	mΩ
gfs	Forward Transconductance	VDS = 5V, ID =20A	--	85	--	S

Dynamic Electrical Characteristics@Tj = 25°C (unless otherwise stated)

C_{iss}	Input Capacitance	V_{DS}=30V,V_{GS}=0V , f=1MHz	--	2122	--	pF
C_{oss}	Output Capacitance		--	440	--	pF
C_{rss}	Reverse Transfer Capacitance		--	4.4	--	pF
R_g	Gate Resistance	V_{GS} = 0V, V_{DS}= 0V, f = 1MHz	--	1.4	--	Ω
Q_g (10V)	Total Gate Charge	V_{DS}=30V, I_D=20A , V_{GS}=10V	--	31	--	nC
Q_{gs}	Gate-Source Charge		--	4.8	--	nC
Q_{gd}	Gate-Drain Charge		--	5.4	--	nC

Switching Characteristics

Td(on)	Turn-on Delay Time	V_{DD}=30V, V_{GS}=10V R_L=1.5Ω, R_G=6Ω,	--	8.0	--	ns
Tr	Turn-on Rise Time		--	5.1	--	ns
Td(off)	Turn-Off Delay Time		--	38	--	ns
Tf	Turn-Off Fall Time		--	14.8	--	ns

Source- Drain Diode Characteristics@ T_j = 25°C (unless otherwise stated)

V_{SD}	Forward on voltage	I_S=1A,V_{GS}=0V	--	0.7	1.0	V
Trr	Reverse Recovery Time	I_F=20A di/dt=100A/μs	--	37	--	ns
Qrr	Reverse Recovery Charge		--	43	--	nC

NOTE: ① Repetitive rating; pulse width limited by max junction temperature.

② Limited by T_{Jmax}, s tarting T_J = 2 5°C, L = 100uH,V_{GS} = 10V.V_{DS} = 30V ,Part not recommended for use above this value

③ The power dissipation P_{DSM} i s based on $R_{\theta JA}$ a nd the maximum allowed junction temperature of 150°C.

④ Pulse width ≤ 380μs; duty cycle≤ 2%.

Typical Characteristics

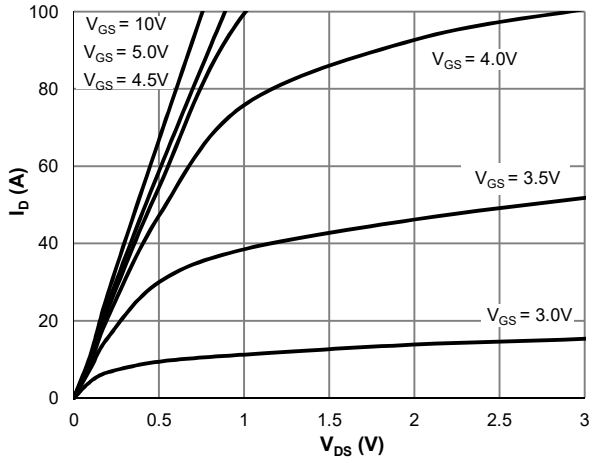


Figure 1: Saturation Characteristics

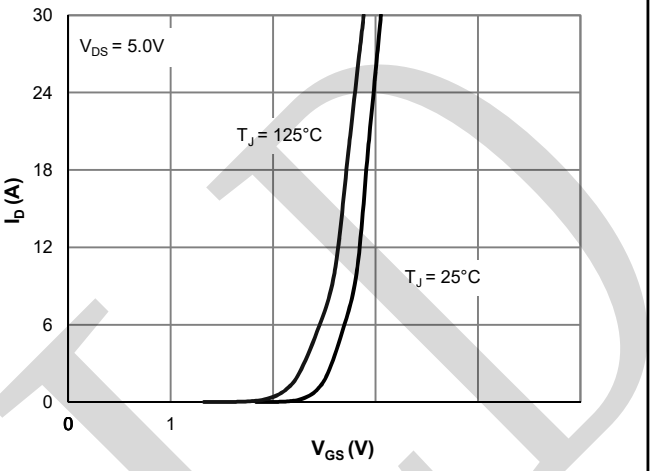


Figure 2: Transfer Characteristics

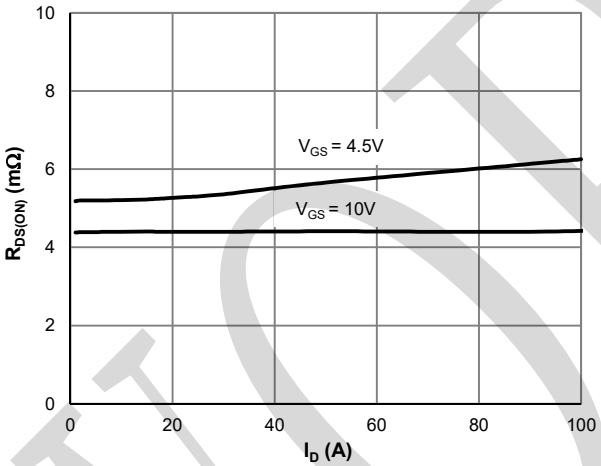


Figure 3: $R_{DS(ON)}$ vs. Drain Current

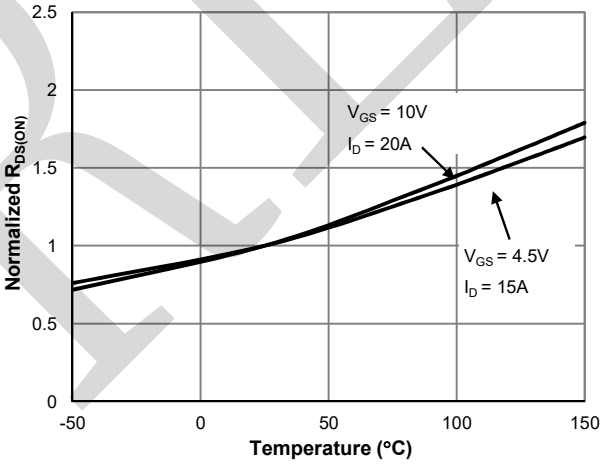


Figure 4: $R_{DS(ON)}$ vs. Junction Temperature

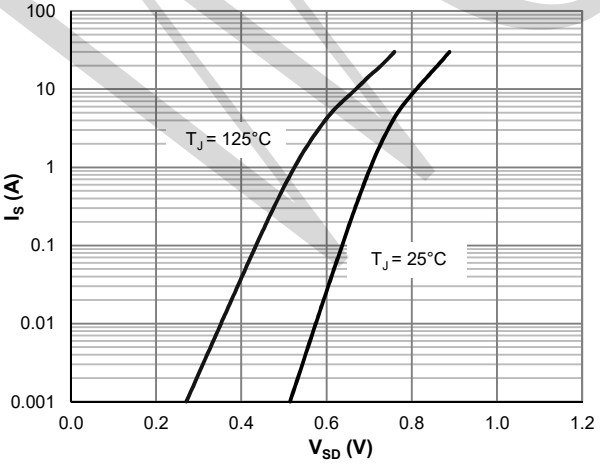


Figure 5: Body-Diode Characteristics

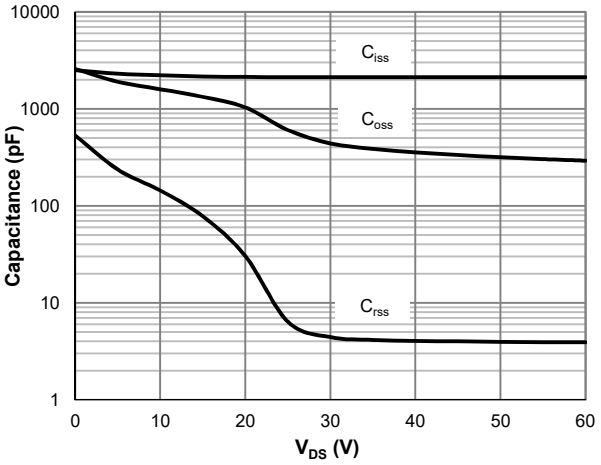


Figure 6: Capacitance Characteristics

Typical Characteristics

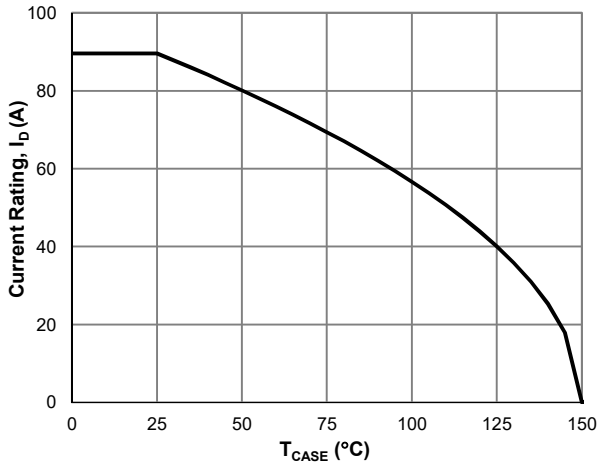


Figure 7: Current De-rating

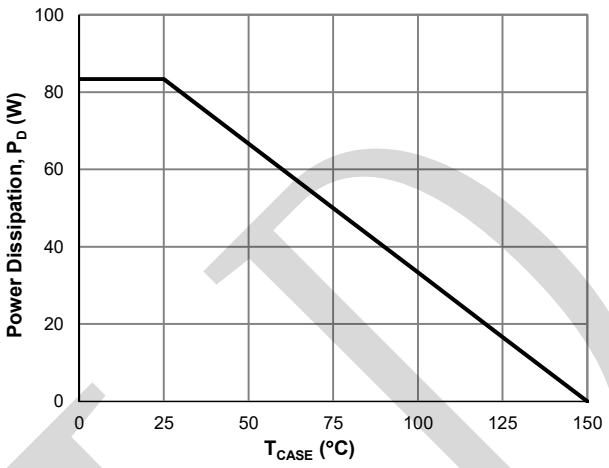


Figure 8: Power De-rating

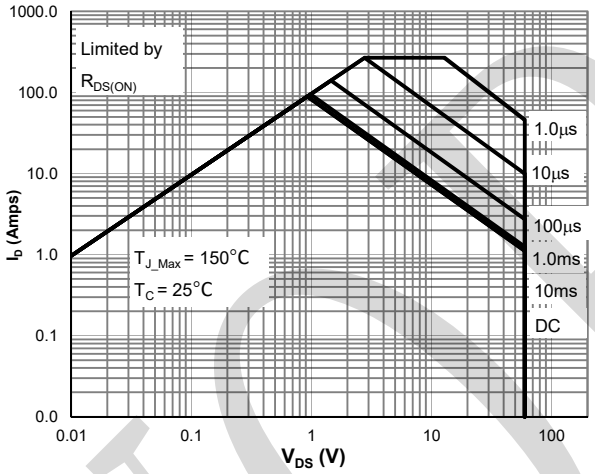


Figure 9: Maximum Safe Operating Area

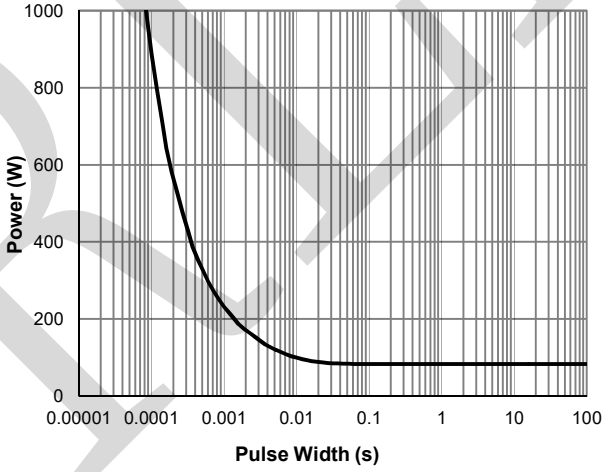


Figure 10: Single Pulse Power Rating, Junction-to-Case

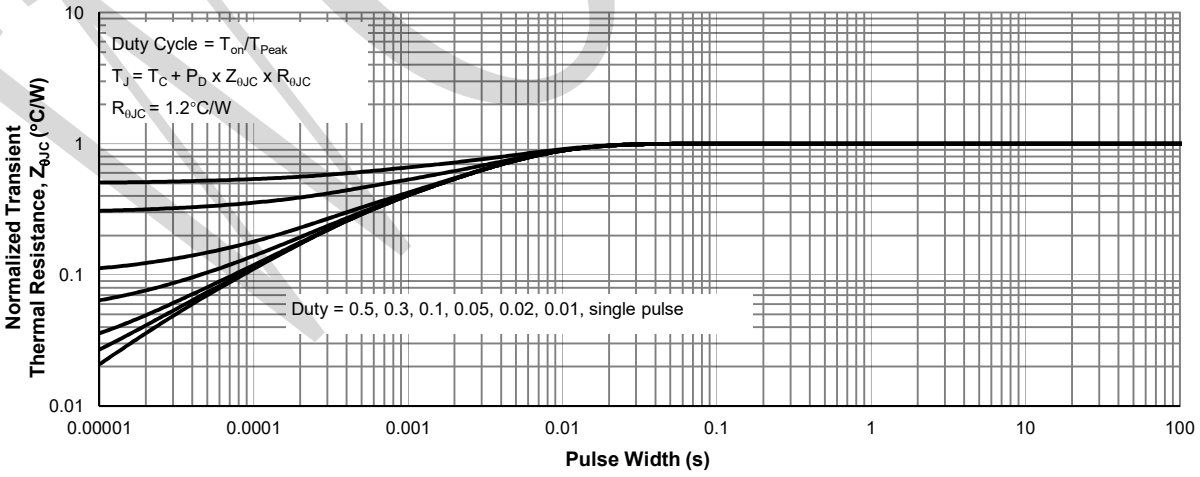
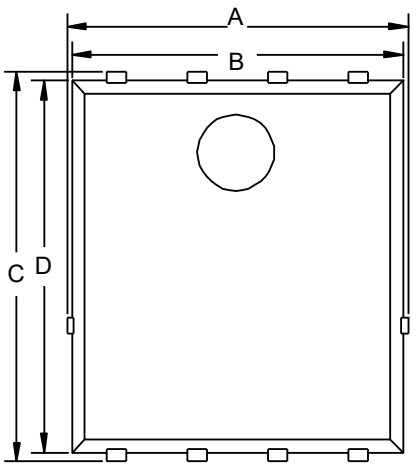
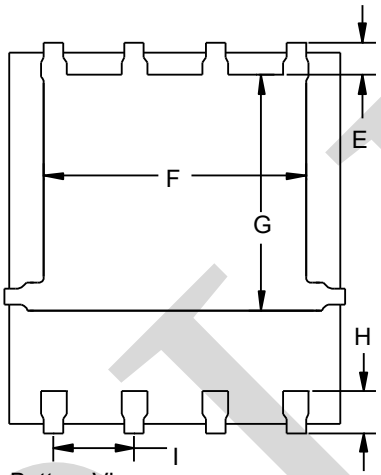


Figure 11: Normalized Maximum Transient Thermal Impedance

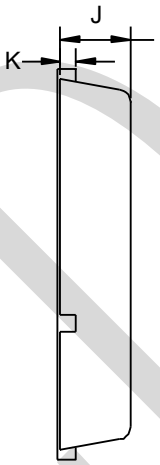
PACKAGE OUTLINE DIMENSIONS



Top View



Bottom View

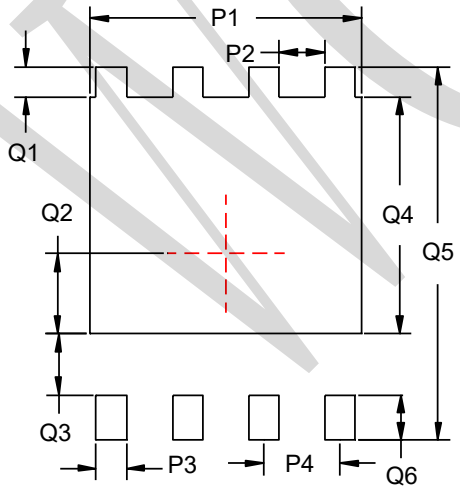


Side View

PDFN5x6 mechanical data

UNIT		A	B	C	D	E	F	G	H	I	J	K
mm	min	4.90	4.8	5.90	5.66	0.60	3.90	3.30	0.53	1.27	0.9	0.254
	max	5.55	5.4	6.35	6.06		4.32	3.92	0.76		1.2	
mil	min	192.9	188.9	232.3	222.8	23.6	153.5	129.9	20.8	50.0	35.4	10.0
	max	218.5	212.6	250.0	238.6		170.1	154.3	29.9		47.2	

PDFN5x6 Suggested Pad Layout



UNIT		P1	P2	P3	P4	Q1
mm	min	4.52	0.76	0.51	1.27	0.50
mil	min	177.9	29.9	20.07	50.0	20.0

UNIT		Q2	Q3	Q4	Q5	Q6
mm	min	1.34	1.02	3.97	6.25	0.76
mil	min	52.75	40.15	156.30	246.06	29.92